

AMENDMENTS TO THE CLAIMS

Claims 1-14 and 20-35 (cancelled)

15. (original) A method of forming a magnetic tunnel junction element

comprising:

forming a free ferromagnetic layer;

forming a pinned ferromagnetic layer,

forming a tunnel junction barrier layer between the free and pinned layers;

forming another ferromagnetic layer in flux communication with the pinned layer which reduces demagnetization coupling between the pinned ferromagnetic layer and the free ferromagnetic layer.

16. (original) A method as in claim 15, wherein the pinning layer comprises a layer of at least one of IrMn and PtMn.

17. (original) A method as in claim 15, wherein at least one of the free and pinned layers comprises a layer of at least one of Co-Fe and Ni-Fe.

18. (original) A method as in claim 15, further comprising forming conductive layers in electrical contact with the free layer and the offset layer.

19. (original) A method of forming a magnetic memory element comprising:

forming a free ferromagnetic layer;

forming a pinned ferromagnetic layer;

forming a tunnel junction barrier layer between the free and pinned layers;

forming an antiferromagnetic layer for pinning the pinned layer;

and

forming another ferromagnetic layer on a side of said antiferromagnetic layer which is opposite a side forming said pinned layer, said another ferromagnetic layer receiving flux coupling between said free and pinned layers.